Doping of Self-Catalyzed Nanowires under the Influence of Droplets

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Supporting information 1:

Figure S1. SEM image of GaAs NWs grown with a 60 mins Be doped duration (nominal concentration 1.6×10^{18}/cm^3) and then followed by a 20 mins non-doped duration. The Ga droplet is on the exact top of the NW.
Supporting information 2:

Figure S2. Oxygen distribution map in the NW cross-section shown in Figure 3a.